

University of California at Berkeley
 College of Engineering
 Department of Electrical Engineering
 and Computer Sciences

R. T. Howe (Spring 1993)

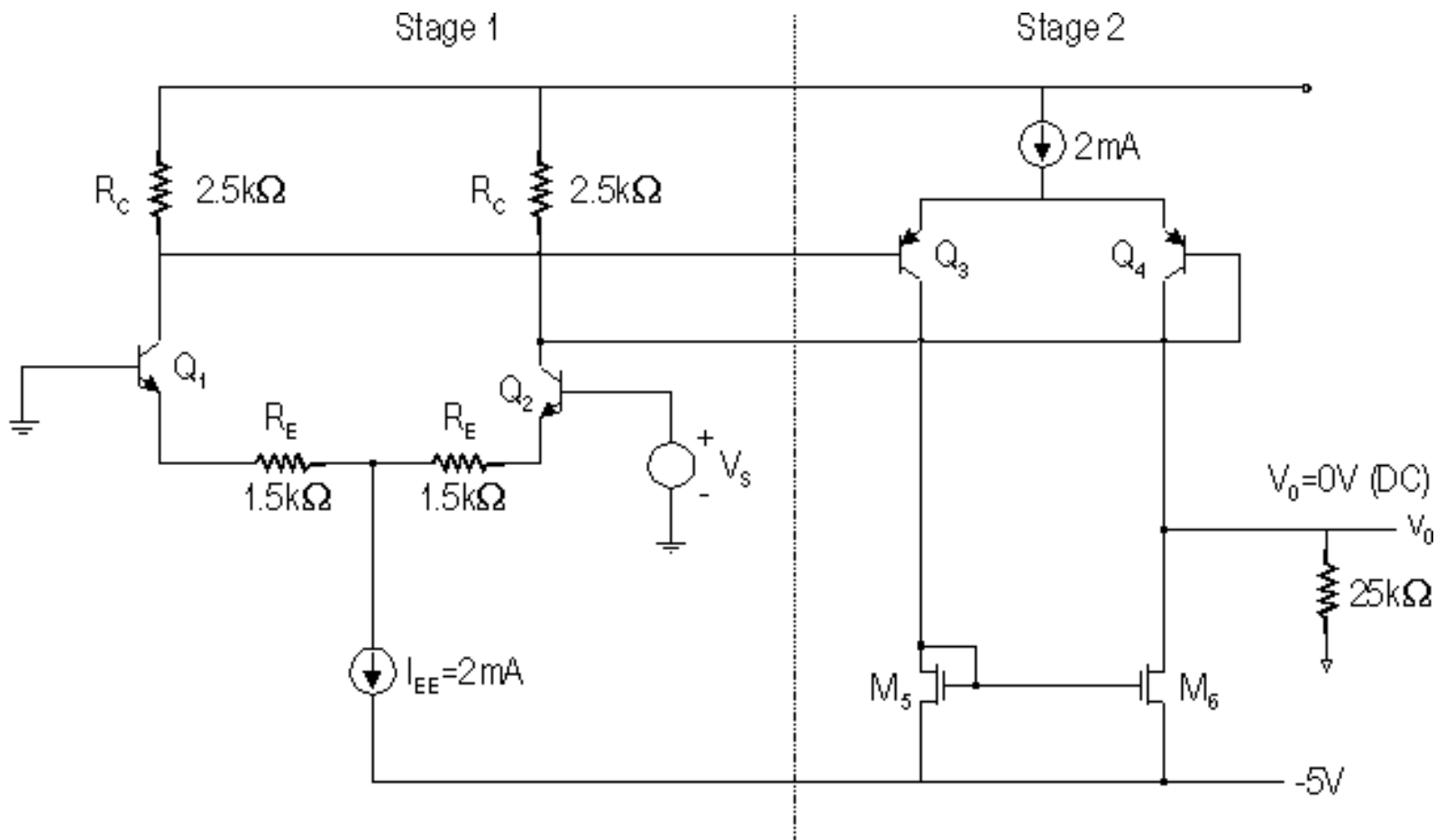
EECS 105
Final Examination: May 17, 1993

Ground Rules:

- Closed book; three 8½ " x 11" crib sheets (both sides)
- Do all work on exam pages
- Answers within $\pm 10\%$ of the correct answer will receive full credit.
- Default bipolar transistor parameters:
 npn: $\beta_n = 100$, $V_{A_n} = 100 \text{ V}$, $C_{\pi} = 15 \text{ pF}$, $C_{\mu} = 1 \text{ pF}$
 pnp: $\beta_p = 50$, $V_{A_p} = 50 \text{ V}$, $C_{\pi} = 30 \text{ pF}$, $C_{\mu} = 2 \text{ pF}$
- Default MOS transistor parameters:
 NMOS: $\mu_n C'_{ox} = 25 \mu\text{A V}^{-2}$, $\lambda_n = 0.01 \text{ V}^{-1}$, $V_{T_n} = 1 \text{ V}$
 PMOS: $\mu_p C'_{ox} = 10 \mu\text{A V}^{-2}$, $\lambda_p = 0.02 \text{ V}^{-1}$, $V_{T_p} = -1 \text{ V}$

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1. Two-Stage BiCMOS Differential Amplifier [20 points]



(a) [2 points] Draw the differential half circuit for *Stage 1*.

(b) [4 points] Draw the differential two-port small-signal model for *Stage 1* and find the numerical values of its parameters.

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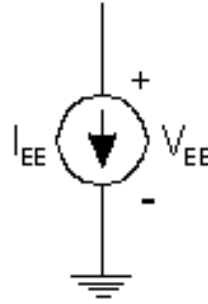
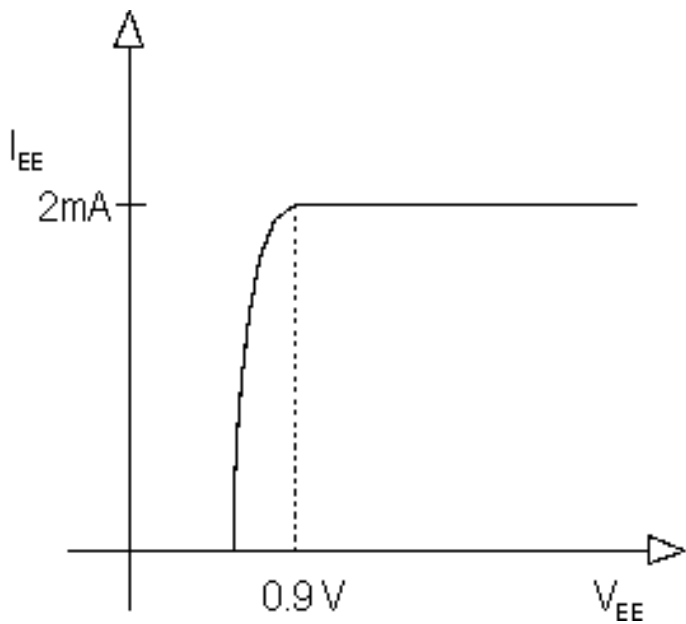
(c) [4 points] Draw the differential two-port small-signal model for *Stage 2* and find the numerical values of its parameters.

(d) [4 points] Find the numerical value of the small-signal gain v_o/s .

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(e) [2 points] What is the maximum DC common-mode input voltage, $V_{CM,max}$, for which all devices are forward active (BJT) or saturated (MOS)?

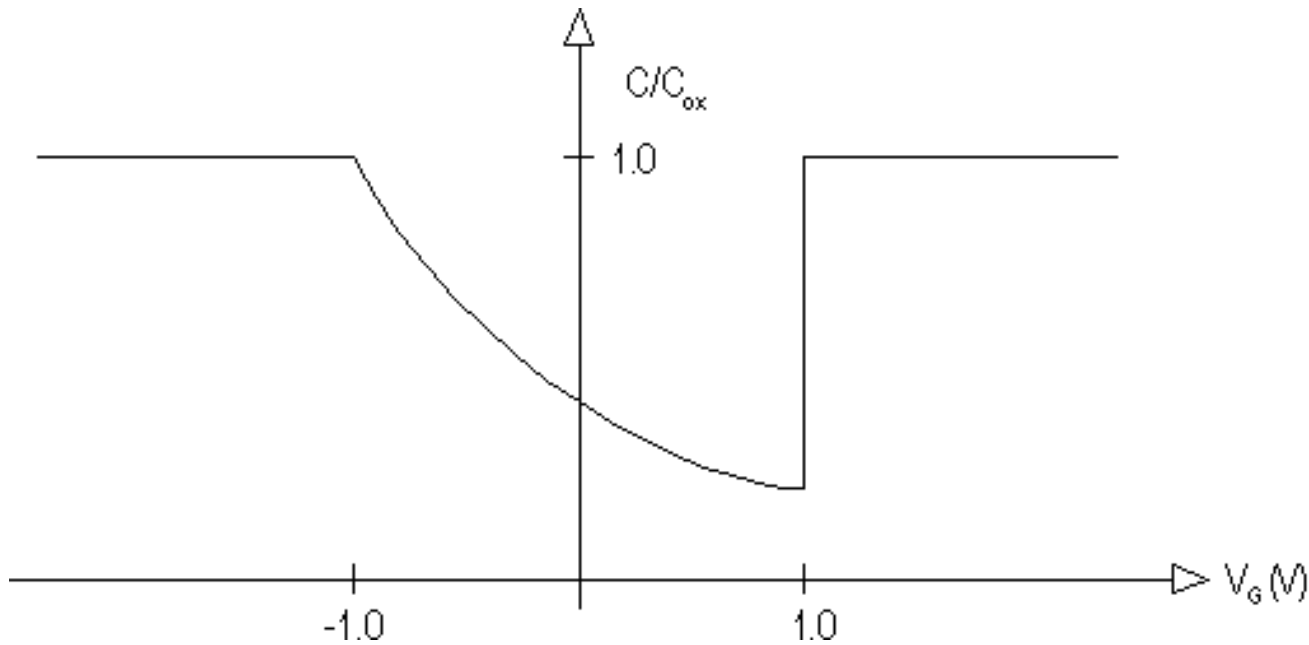
(f) [2 points] What is the minimum DC common-mode input voltage, $V_{CM,min}$, for which all devices are forward active (BJT) or saturated (MOS)?



(g) [2 points] What is the DC power dissipation for this amplifier?

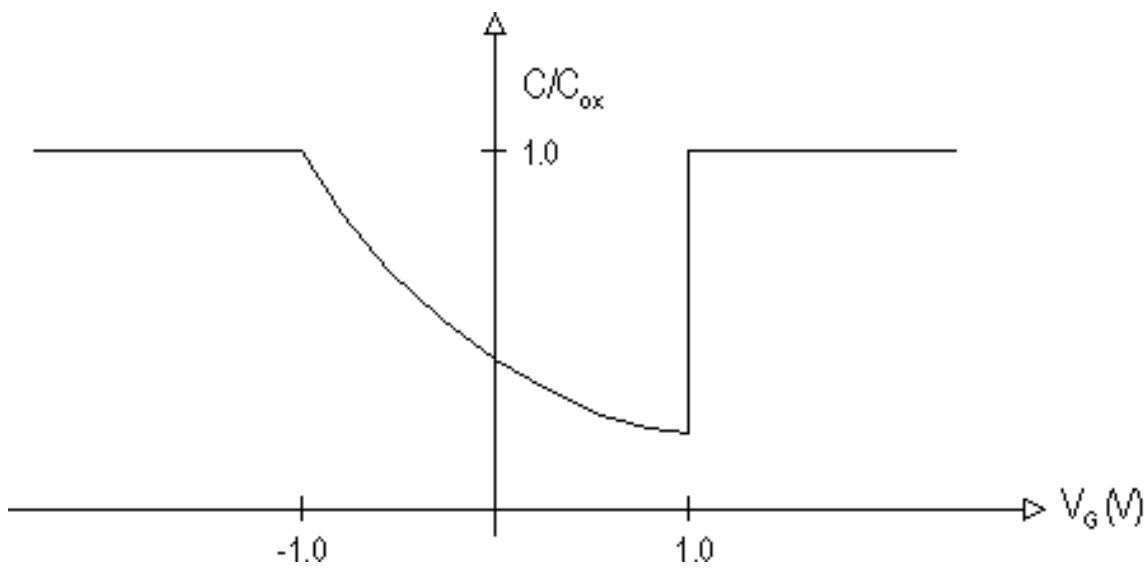
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2. Pictorial MOS Electrostatics [20 points]

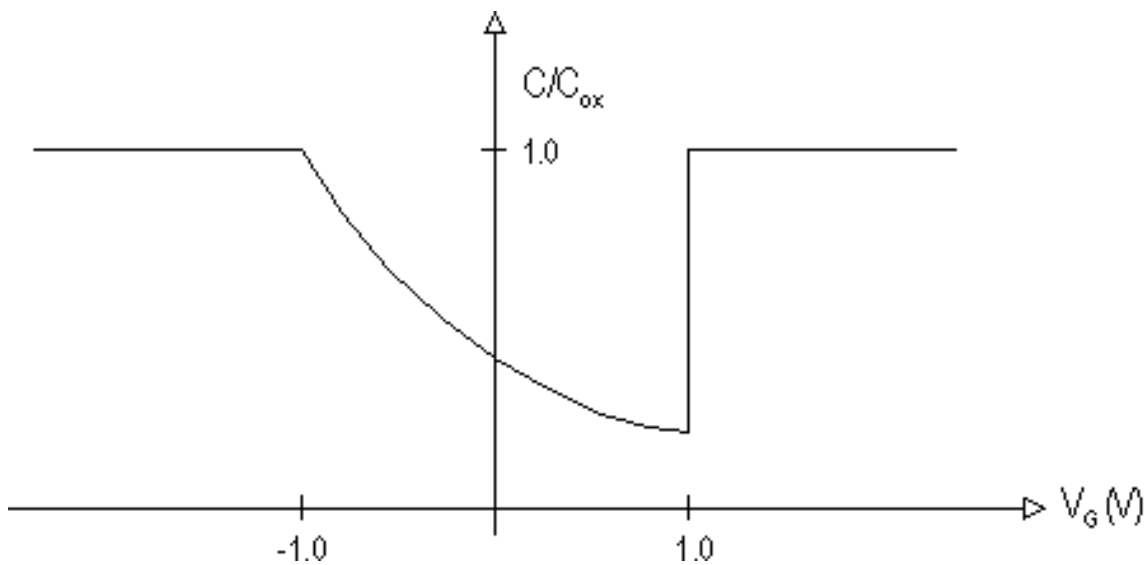


A MOS C-V curve is shown above for an n+ polysilicon gate and a p-type substrate, with $N_a = 1 \times 10^{16} \text{ cm}^{-3}$.

(a) [5 points] Sketch below the C-V curve for this structure when the oxide thickness t_{ox} is reduced. Your plot should be *qualitatively correct* -- the original C-V curve is reproduced to make comparison easier.

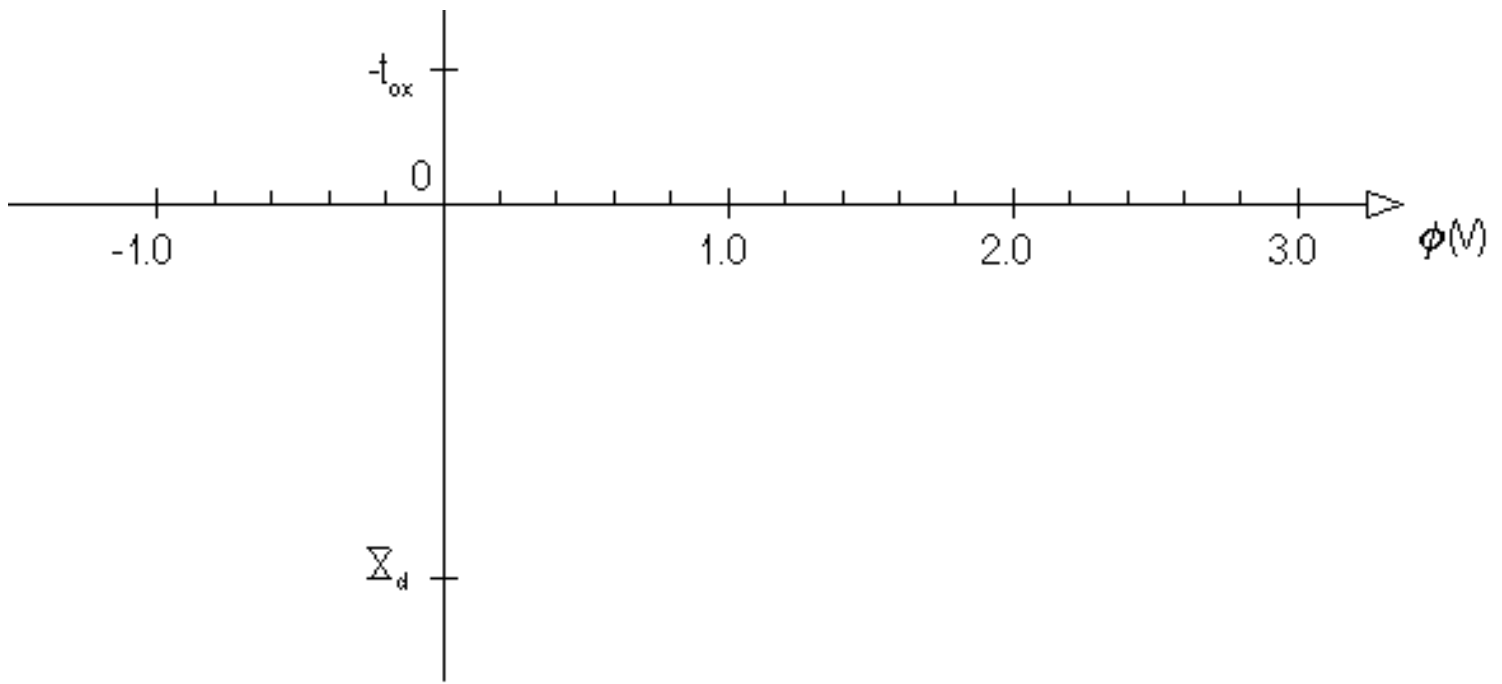


(b) [5 points] Sketch below the C-V curve for the *complementary* structure, for which the gate is p+ polysilicon and the substrate is n-type with $N_a = 1 \times 10^{16} \text{ cm}^{-3}$. Your plot should be *qualitatively correct* -- the original C-V curve is reproduced to make comparison easier.

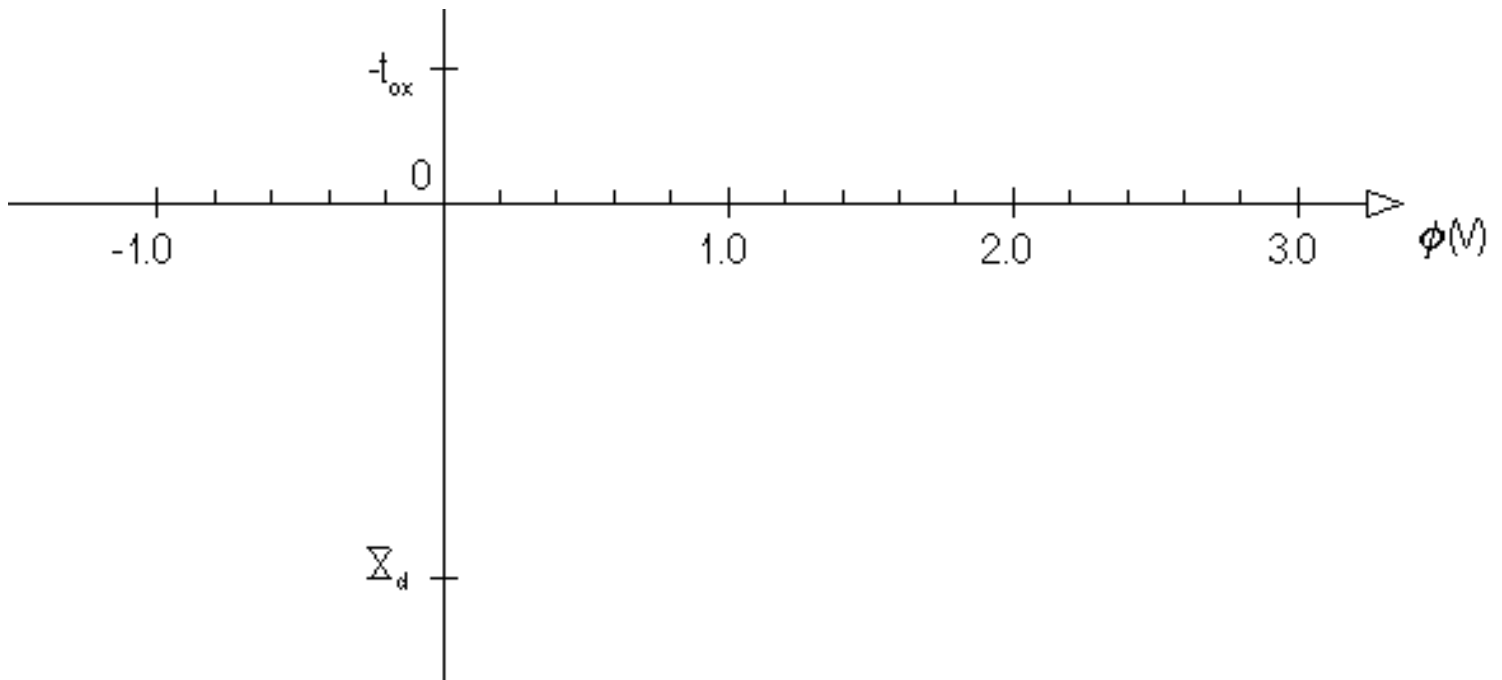


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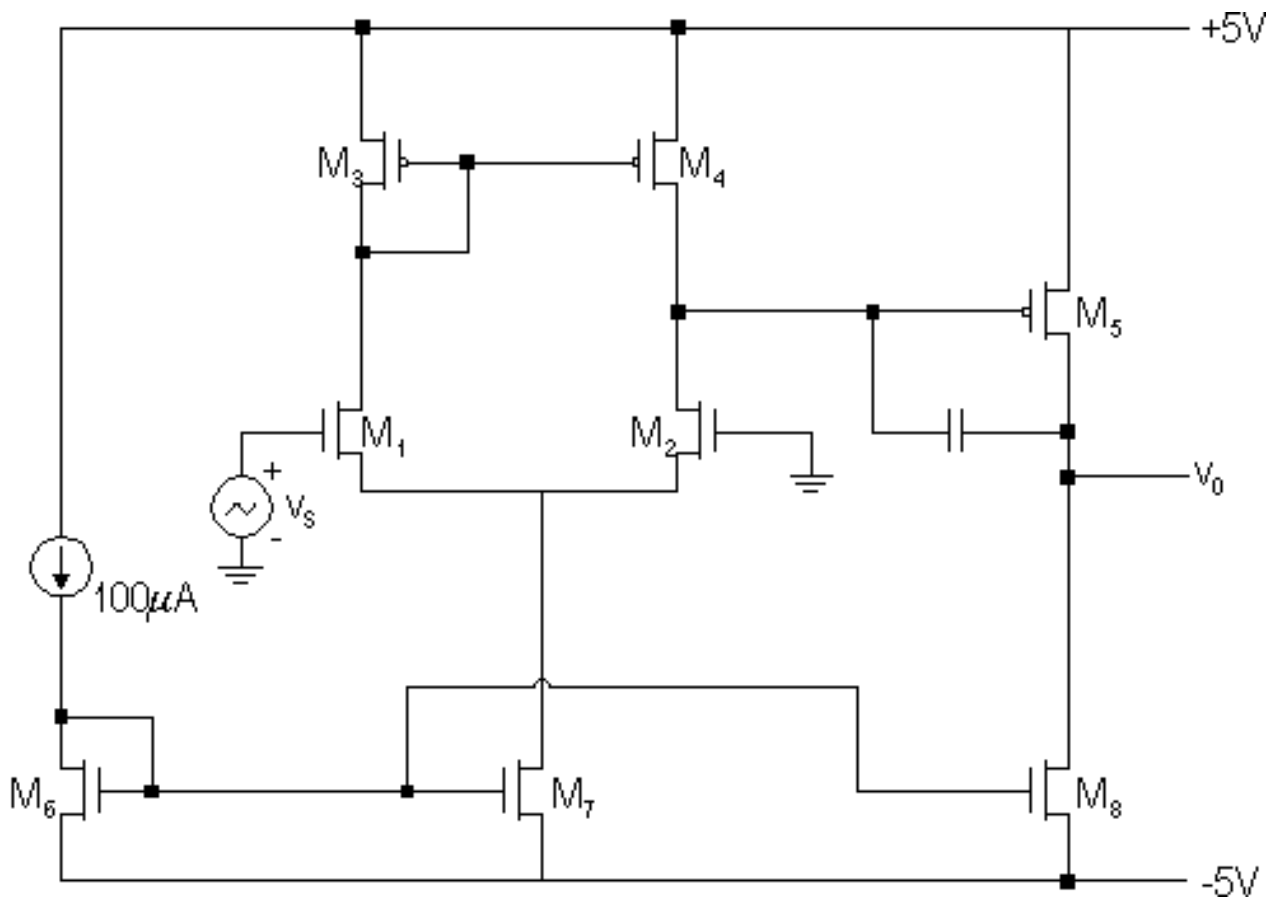
(c) [5 points] Sketch the electrostatic potential through the original structure when it is in *thermal equilibrium* ($V_G = 0 \text{ V}$). Given the polysilicon potential is $\phi_{n+} = 0.55 \text{ V}$, surface potential $\phi_s = \phi(x=0) = 0 \text{ V}$, $x=0$ corresponds to the oxide/silicon interface.



(d) [5 points] Sketch the electrostatic potential through the original structure when $V_G=2V$



3. MOS Amplifier Frequency Response [20 points]



Given:

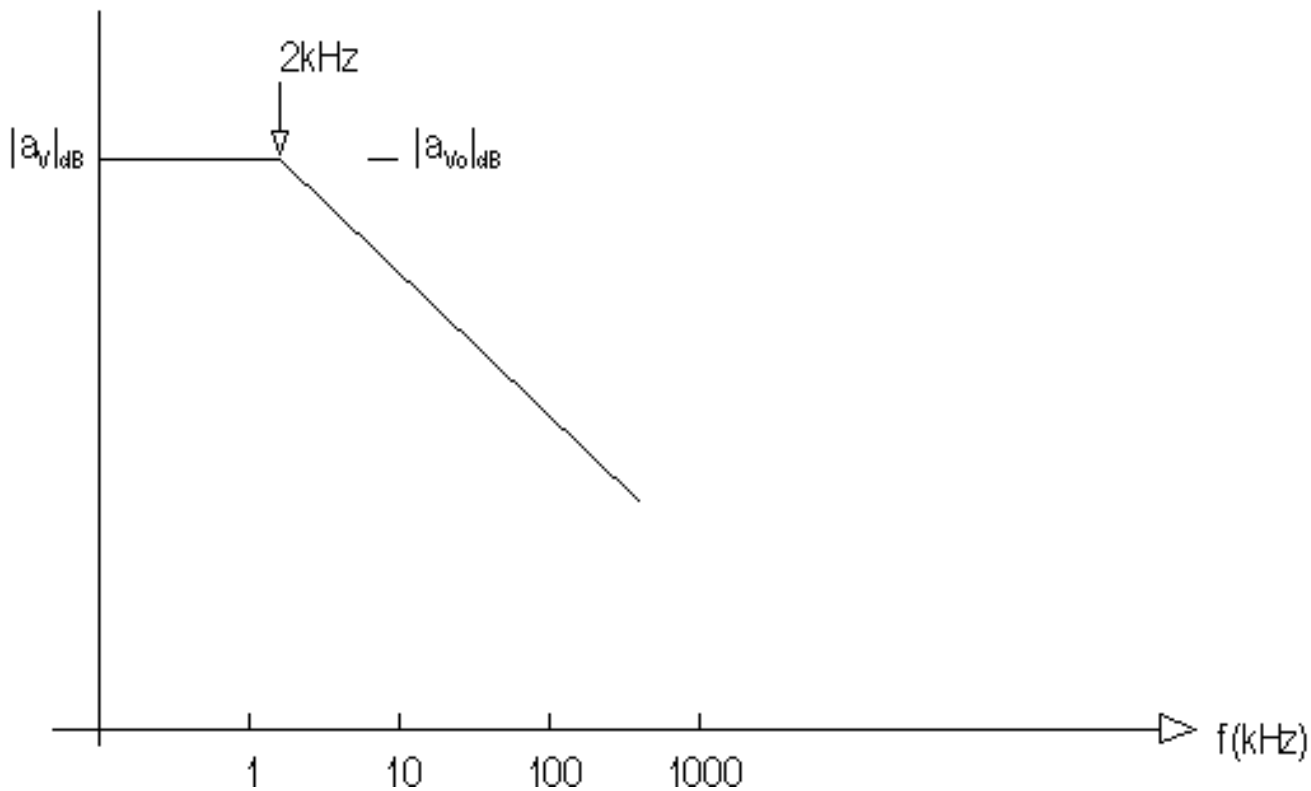
$$\left(\frac{W}{L}\right)_7 = 2\left(\frac{W}{L}\right)_8 = 2\left(\frac{W}{L}\right)_6 \\ = 20$$

$$\left(\frac{W}{L}\right)_1 = \left(\frac{W}{L}\right)_2 = \left(\frac{W}{L}\right)_3 \\ = \left(\frac{W}{L}\right)_4 = \left(\frac{W}{L}\right)_5 = 50$$

- (a) [4 points] Find the DC voltages at the drain of M2 and at the source of M2.
- (b) [4 points] Find the small-signal voltage gain $a_{v0} = v_o/v_s$ at low frequencies (consider C_c open).

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- (c) [4 points] Given that the magnitude (in dB) plot for the voltage gain has a pole at 2kHz (see plot), find the numerical value of C_c . You may assume that any Miller capacitor dominates all other device capacitors (e.g., C_{gs}).

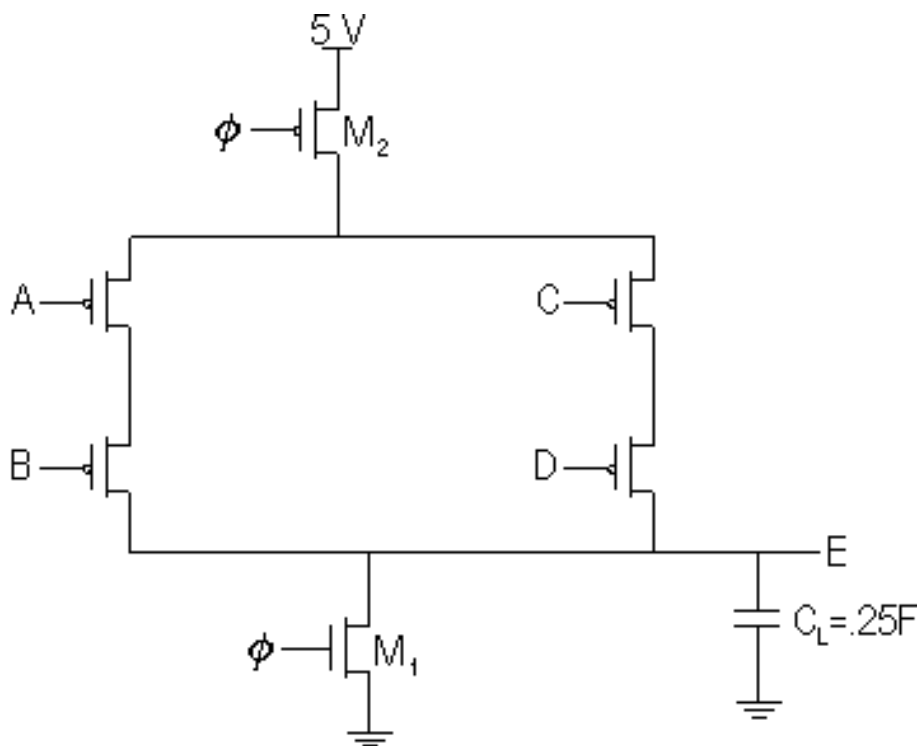


(d) [4 points] Find the frequency for which the magnitude of the small-signal voltage gain $|a_v|_{dB}=0$ dB. If you couldn't solve part (b), assume that $a_{v0}=14,000$.

(e) [4 points] Given that the channel length of all MOSFETs is $L=3 \mu\text{m}$ and that the oxide capacitance per unit area is $C_{v0}=14,000$.

(d) [4 points] Given that the channel length of all MOSFETs is $L=3 \mu\text{m}$ and that the oxide capacitance per unit area is $C_{ox}=0.5 \text{ fF}/\mu\text{m}^2$ ($1 \text{ fF}=1\text{E}-15 \text{ F}$), find the differential input *capacitance* of this op amp.

4. Dynamic MOS Logic [20 points]



$$\left(\frac{W}{L}\right)_{1,2} = 50$$

$$\left(\frac{W}{L}\right)_{A,B,C,D} = 5$$

(a) [4 points] What logic function is implemented by this dynamic logic gate? Use the + sign for "OR", a dot for "AND", and an overscore for "NOT". There is no need to simplify the expression. *Hint*: transistor M_1 functions to "pre-ground" the load capacitance C_L , using clock waveform $\phi(t)$.

(b) [4 points] How short a 5-V clock pulse (length T_ϕ) can be used to pre-ground the load capacitance, assuming that the minimum T_ϕ is 5 times the propagation delay found in discharging C_L from 5 V to 0 V? *Hint*: consider the appropriate transistor to be saturated in finding the propagation delay.

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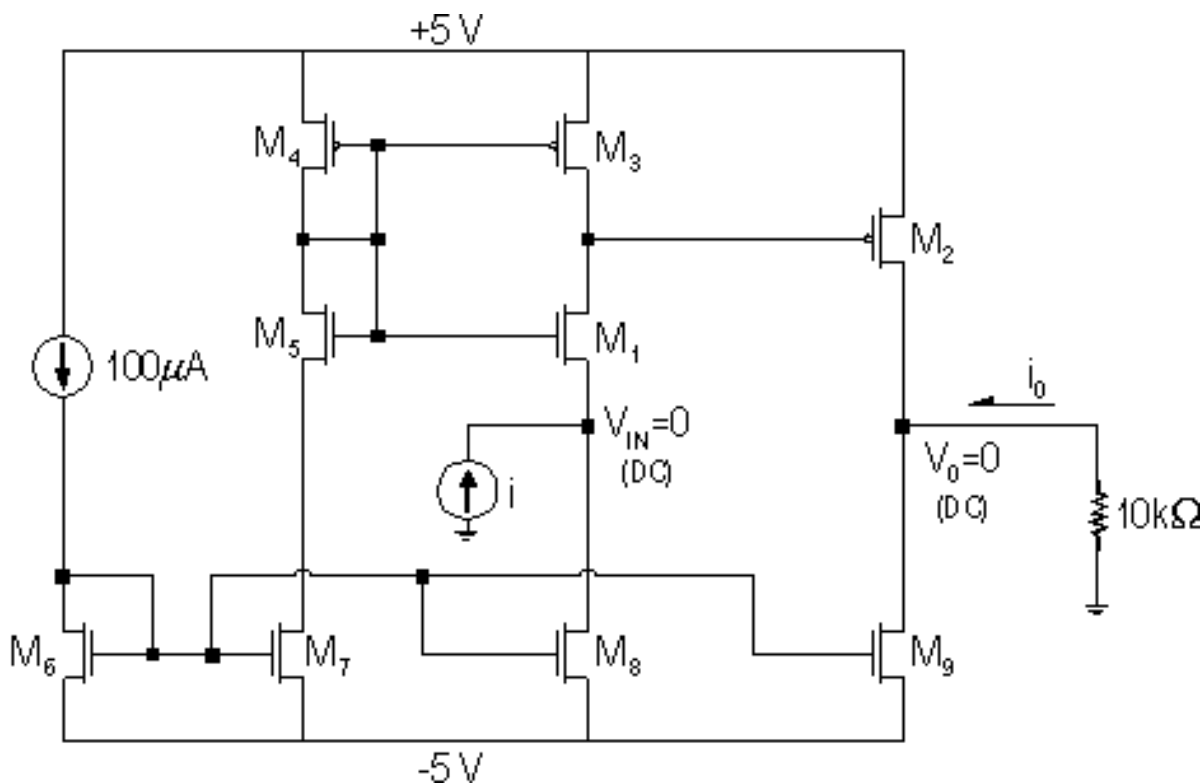
(c) [4 points] Sketch $v_E(t)$ on the graph below, for the case where A, B, C, and D are 0 V when $t = T_\phi$. You are given that $v_E(0^-) = 5$ V just before the clock transitions to 5 V at $t = 0$.

(d) [4 points] What is the propagation delay for the situation in part (c) (all inputs low when the clock goes low)? You can consider that M_2 is so wide that it functions as a short-circuit when it's "on".

(e) [4 points] What is the propagation delay when A, B, D = 0 and C = 1 (5 V) when the clock $\phi(t)$ goes low? If you couldn't solve part (c), assume that its answer was $t_p = 1$ ns.

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5. Small-signal CMOS current amplifier [20 points]



$$\left(\frac{W}{L}\right)_1 = \left(\frac{W}{L}\right)_2 = \left(\frac{W}{L}\right)_5 = 50$$

$$\text{rest have } \left(\frac{W}{L}\right) = 20$$

(a) [4 points] Redraw the schematic, replacing all transistor current sources by the current-source symbol (with the numerical value indicated) and all transistor voltage sources by batteries (with the numerical value indicated).

(b) [4 points] What is the numerical value of the input resistance R_i of this current amp?

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(c) [4 points] What is the numerical value of the output resistance (don't include the load resistor, of course!) for this current amp?

(d) [4 points] What is the short-circuit current gain A_i (v_o a small-signal short to ground) for this current amplifier? Draw the two-port model for the amp.

(e) [4 points] What is the overall current gain i_o/i_{in} with the $100 \text{ k}\Omega$ load resistor connected to the amplifier?

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